```
=> d his ful

     (FILE 'HOME' ENTERED AT 12:44:45 ON 11 FEB 2009)

     FILE 'HCAPLUS' ENTERED AT 12:44:55 ON 11 FEB 2009
L1             1 SEA SPE=ON  ABB=ON  PLU=ON  US20080241753/PN
                 D L1 ALL
                 SAV L1 LEE004/A
                 SEL L1 RN

     FILE 'REGISTRY' ENTERED AT 12:45:36 ON 11 FEB 2009
L2             9 SEA SPE=ON  ABB=ON  PLU=ON  (138529-81-4/BI OR 144317-44-
                 2/BI OR 17464-88-9/BI OR 188557-77-9/BI OR 3089-11-0/BI
                 OR 357164-86-4/BI OR 4356-60-9/BI OR 475115-04-9/BI OR
                 66003-78-9/BI)
                 D SCA
                 SAV L2 LEE004A/A

     FILE 'LREGISTRY' ENTERED AT 12:49:12 ON 11 FEB 2009
L3               STR

     FILE 'REGISTRY' ENTERED AT 12:52:48 ON 11 FEB 2009
L4            50 SEA SSS SAM L3


     FILE 'LREGISTRY' ENTERED AT 14:01:00 ON 11 FEB 2009
L5               STR L3

     FILE 'REGISTRY' ENTERED AT 14:04:57 ON 11 FEB 2009
L6            50 SEA SSS SAM L5
L7            50 SEA SSS SAM L5

L8         91465 SEA SSS FUL L5
                 SAV L8 LEE004B/A

     FILE 'LREGISTRY' ENTERED AT 14:09:24 ON 11 FEB 2009
L9               STR L5

     FILE 'REGISTRY' ENTERED AT 14:12:36 ON 11 FEB 2009
L10            2 SEA SPE=ON  ABB=ON  PLU=ON  L2 AND L8
                 D SCA

     FILE 'LREGISTRY' ENTERED AT 14:13:11 ON 11 FEB 2009
L11              STR L5

     FILE 'REGISTRY' ENTERED AT 14:14:33 ON 11 FEB 2009
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L12           1 SEA SUB=L8 SSS SAM (L9 AND L11)


     FILE 'LREGISTRY' ENTERED AT 14:17:00 ON 11 FEB 2009
L13             STR L9
L14             STR L11

     FILE 'REGISTRY' ENTERED AT 14:47:24 ON 11 FEB 2009
L15           3 SEA SUB=L8 SSS SAM (L13 AND L14)

L16         136 SEA SUB=L8 SSS FUL (L13 AND L14)
                SAV L16 LEE004D/A

     FILE 'HCAPLUS' ENTERED AT 14:49:17 ON 11 FEB 2009
L17          76 SEA SPE=ON  ABB=ON  PLU=ON  L16
L18      125035 SEA SPE=ON  ABB=ON  PLU=ON  RESIST# OR PHOTORESIST? OR
                PHOTO#(W)RESIST?
L19          10 SEA SPE=ON  ABB=ON  PLU=ON  L17 AND L18
L20      342967 SEA SPE=ON  ABB=ON  PLU=ON  CROSSLINK? OR CROSS#(W)LINK?

L21           6 SEA SPE=ON  ABB=ON  PLU=ON  L17 AND L20
L22           5 SEA SPE=ON  ABB=ON  PLU=ON  L21 NOT L19

                    D L21 AN 6
                D L19 10 AN
L23           1 SEA SPE=ON  ABB=ON  PLU=ON  L17 AND PY<=2004 NOT P/DT
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     FILE 'REGISTRY' ENTERED AT 15:10:50 ON 11 FEB 2009
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     FILE 'HCAPLUS' ENTERED AT 15:16:46 ON 11 FEB 2009
L26          13 SEA SPE=ON  ABB=ON  PLU=ON  L25
L27           6 SEA SPE=ON  ABB=ON  PLU=ON  L26 NOT (L19 OR L22)

     FILE 'REGISTRY' ENTERED AT 15:17:55 ON 11 FEB 2009

                SAV L25 LEE404F/A




     FILE HOME

     FILE HCAPLUS
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FILE COVERS 1907 - 11 Feb 2009 VOL 150 ISS 7
FILE LAST UPDATED: 10 Feb 2009 (20090210/ED)

HCAplus now includes complete International Patent Classification (I reclassification data for the third quarter of 2008.

CAS Information Use Policies apply and are available at:

http://www.cas.org/legal/infopolicy.html

This file contains CAS Registry Numbers for easy and accurate substance identification.

FILE REGISTRY
Property values tagged with IC are from the ZIC/VINITI data file provided by InfoChem.

STRUCTURE FILE UPDATES: 9 FEB 2009 HIGHEST RN 1103577-63-4
DICTIONARY FILE UPDATES: 9 FEB 2009 HIGHEST RN 1103577-63-4

New CAS Information Use Policies, enter HELP USAGETERMS for details.

TSCA INFORMATION NOW CURRENT THROUGH July 5, 2008.

Please note that search-term pricing does apply when conducting SmartSELECT searches.

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http://www.cas.org/support/stngen/stndoc/properties.html

FILE LREGISTRY
LREGISTRY IS A STATIC LEARNING FILE

NEW CAS INFORMATION USE POLICIES, ENTER HELP USAGETERMS FOR DETAILS.

FILE STNGUIDE
FILE CONTAINS CURRENT INFORMATION.
LAST RELOADED: Feb 6, 2009 (20090206/UP).

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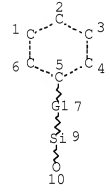

REP G1=(0-6) C
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DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:
RSPEC 5
NUMBER OF NODES IS 9

STEREO ATTRIBUTES: NONE
L8 91465 SEA FILE=REGISTRY SSS FUL L5

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SEARCH TIME: 00.00.01

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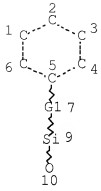
L5 STR



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DEFAULT MLEVEL IS ATOM
DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:
RSPEC 5
NUMBER OF NODES IS 9

STEREO ATTRIBUTES: NONE
L8 91465 SEA FILE=REGISTRY SSS FUL L5
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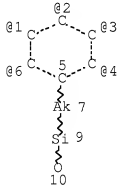

VPA 13-1/2/3/4/6 U
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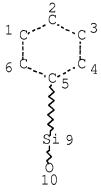
DEFAULT MLEVEL IS ATOM
DEFAULT ECLEVEL IS LIMITED
ECOUNT IS M1-X5 C AT 7

GRAPH ATTRIBUTES:
RSPEC 5
NUMBER OF NODES IS 10

STEREO ATTRIBUTES: NONE
L14 STR



NODE ATTRIBUTES:
DEFAULT MLEVEL IS ATOM
DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:
RSPEC 5
NUMBER OF NODES IS 8

STEREO ATTRIBUTES: NONE
L16 136 SEA FILE=REGISTRY SUB=L8 SSS FUL (L13 AND L14)

100.0% PROCESSED 76875 ITERATIONS 136 ANSWERS
SEARCH TIME: 00.00.01

=> d l19 1-10 bib abs hitstr hitind

L19 ANSWER 1 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2008:1243897 HCAPLUS Full-text
DN 149:458344
TI Nanoimprint resists containing substituted phenyl-containing silsesquioxanes and their patterns and patterning
IN Takeuchi, Yoshiyuki; Ishikawa, Kiyoshi
PA Tokyo Ohka Kogyo Co., Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 15pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 2

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2008246876	A	20081016	JP 2007-91695	20070330
WO 2008126523	A1	20081023	WO 2008-JP53988	20080305

W: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW

RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM

PRAI JP 2007-91695 A 20070330
JP 2007-227089 A 20070831
JP 2007-227090 A 20070831

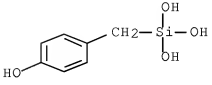
AB Title resists contain silsesquioxanes containing Si(R2-p-C6H4OR1)O2/3 [R1 = H, C1-5 alkyl; R2 = single bond, C1-5 alkylene]. Because of the silsesquioxanes, the nanoimprint patterns, useful for lenses, show high transfer accuracy and good mold-release properties.

IT 475115-04-9 1002099-61-7
RL: TEM (Technical or engineered material use); USES (Uses)
(assumed monomers; substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)

RN 475115-04-9 HCAPLUS
CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8
CMF C7 H10 O4 Si



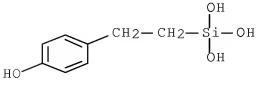
CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

RN 1002099-61-7 HCAPLUS
CN Silanetriol, 1-[2-(4-hydroxyphenyl)ethyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

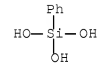
CM 1

CRN 546114-69-6
CMF C8 H12 O4 Si



CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si



CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
ST hydroxybenzylsilanetriol phenylsilanetriol copolymer nanoimprint resist transfer accuracy
IT Silsesquioxanes
RL: TEM (Technical or engineered material use); USES (Uses)
(Me, OCD T 9; substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)
IT Silsesquioxanes
RL: TEM (Technical or engineered material use); USES (Uses)
(hydrogen, OCD T 12; substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)
IT Lithography
(nanoimprint; substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)
IT Silsesquioxanes
RL: TEM (Technical or engineered material use); USES (Uses)
(silicate-; substituted phenyl-containing silsesquioxane nanoimprint
resists showing high transfer accuracy)
IT Resists
(substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)
IT 104133-11-1D, Methylsilanetriol homopolymer, polymers with silicates 157374-41-9, Phenylsilanetriol homopolymer 188557-77-9, p-Hydroxybenzylsilanetriol homopolymer 475115-04-9 1002099-61-7 1043891-50-4 1043891-51-5
RL: TEM (Technical or engineered material use); USES (Uses)
(assumed monomers; substituted phenyl-containing silsesquioxane

nanoimprint resists showing high transfer accuracy)
IT 681-84-5, OCD T 2 51350-55-1, Phenylsilanetriol homopolymer, ladder sru 112627-92-6, OCD Type 7 153315-80-1D, Methylsilanetriol homopolymer, ladder sru, polymers with silicates 188629-68-7, p-Hydroxybenzylsilanetriol homopolymer, ladder sru
RL: TEM (Technical or engineered material use); USES (Uses)
(substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)

L19 ANSWER 2 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2007:1420012 HCAPLUS Full-text
DN 148:67464
TI Method of forming resist pattern by nanoimprint lithography
IN Sato, Kazufumi; Yamada, Tomotaka
PA Tokyo Ohka Kogyo Co., Ltd., Japan
SO PCT Int. Appl., 31pp.
CODEN: PIXXD2
DT Patent
LA Japanese
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2007142088	A1	20071213	WO 2007-JP60956	20070530
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
JP 2007329276	A	20071220	JP 2006-158894	200606 07
PRAI JP 2006-158894	A	20060607		

AB Provided is a method of forming a resist pattern of high aspect ratio excelling in etching resistance using nanoimprint lithog. The method of forming a resist pattern by nanoimprint lithog. comprises the

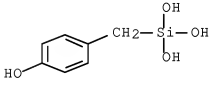
steps of disposing organic layer on support; providing resist layer on the organic layer using chemical amplification type neg. resist composition containing silsesquioxane resin; pressing light transmission allowing mold with partial light shielding portion against the resist layer and thereafter carrying out exposure from the upside of the mold; and detaching the mold.

IT 475115-04-9
RL: TEM (Technical or engineered material use); USES (Uses) (use of molds in forming resist pattern by nanoimprint lithog.)

RN 475115-04-9 HCAPLUS
CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

CC 76-3 (Electric Phenomena)
ST resist pattern nanoimprint lithog silsesquioxane resin; mold exposure

IT Photolithography
(nanoprint; use of molds in forming resist pattern by nanoimprint lithog.)
IT Molds (forms)
Photoresists
Semiconductor device fabrication
(use of molds in forming resist pattern by nanoimprint lithog.)
IT Silsesquioxanes
RL: TEM (Technical or engineered material use); USES (Uses)
(use of molds in forming resist pattern by nanoimprint lithog.)
IT 193345-23-2 227199-92-0 475115-04-3 959860-10-7
RL: TEM (Technical or engineered material use); USES (Uses)
(use of molds in forming resist pattern by nanoimprint lithog.)
RE.CNT 16 THERE ARE 16 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 3 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2006:272812 HCAPLUS Full-text
DN 144:321539
TI Composition for forming antireflective film and electric wiring forming method using same
IN Tanaka, Takeshi; Sakamoto, Yoshinori; Takahama, Masaru
PA Tokyo Ohka Kogyo Co., Ltd., Japan
SO PCT Int. Appl., 34 pp.
CODEN: PIXXD2
DT Patent
LA Japanese
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2006030641	A1	20060323	WO 2005-JP15907	200508 31

W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KM, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD,

TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM

JP 2006084799	A	20060330	JP 2004-269705	200409 16
CN 101010635	A	20070801	CN 2005-80029662	200508 31
TW 279647	B	20070421	TW 2005-94130960	200509 08
KR 2007040827	A	20070417	KR 2007-705137	200703 02
US 20080318165	A1	20081225	US 2007-575299	200703 14

PRAI JP 2004-269705 A 20040916
WO 2005-JP15907 W 20050831

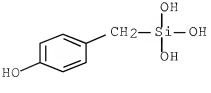
AB Disclosed is an antireflective film-forming material which enables to obtain a large etching rate difference between a resist pattern and an antireflective film. Specifically disclosed is a composition for forming antireflective films which contains a siloxane polymer (A) containing a light absorptive compound group.

IT 475115-04-9
RL: TEM (Technical or engineered material use); USES (Uses)
(composition for forming antireflective film and wiring forming method
using same)

RN 475115-04-9 HCAPLUS
CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 76
IT Antireflective films
Photolithography
Photoresists
Printed circuit boards
(composition for forming antireflective film and wiring forming method
using same)
IT 159873-52-6, Tetramethoxysilane/methyltrimethoxysilane copolymer
475115-04-9
RL: TEM (Technical or engineered material use); USES (Uses)
(composition for forming antireflective film and wiring forming method
using same)
RE.CNT 14 THERE ARE 14 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 4 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2005:1049149 HCAPLUS Full-text
DN 143:356596
TI Negative-working resist composition containing polysilsesquioxane
IN Ando, Tomoyuki
PA Tokyo Ohka Kogyo Co., Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 25 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2005266474	A	20050929	JP 2004-80481	200403 19
	WO 2005091073	A1	20050929	WO 2005-JP4326	200503 11
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	RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
	EP 1726992	A1	20061129	EP 2005-720597	200503 11
	R: DE				
	US 20080241753	A1	20081002	US 2006-593004	200609 14
PRAI	JP 2004-80481	A	20040319		
	WO 2005-JP4326	W	20050311		

AB Disclosed is a neg.-working resist composition comprising (a) a silsesquioxane resin having units of [Si(-R1-C6H4-OH)O3/2] (R1 = C1-5 alkylene) and [SiPhO3/2], (b) an acid-generating compound, and (c) a crosslinking agent.

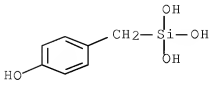
IT 475115-04-9P
RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(neg.-working electron-beam resist composition containing polysilsesquioxane)

RN 475115-04-9 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

IC ICM G03F007-038
ICS C08G077-16; G03F007-075; H01L021-027
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 38
ST neg working electron beam resist compn polysilsesquioxane
IT Electron beam resists
Resists
(neg.-working electron-beam resist composition containing polysilsesquioxane)
IT Silsesquioxanes
RL: TEM (Technical or engineered material use); USES (Uses)
(neg.-working electron-beam resist composition containing polysilsesquioxane)
IT 66003-78-9, Triphenylsulfonium trifluoromethane sulfonate 138529-81-4, Bis(cyclohexylsulfonyl)diazomethane 144317-44-2, Triphenylsulfonium nonafluorobutane sulfonate 357164-86-4
RL: TEM (Technical or engineered material use); USES (Uses)
(acid-generating agent; neg.-working electron-beam resist composition containing polysilsesquioxane)
IT 3089-11-0 4356-60-9 17464-88-9

RL: TEM (Technical or engineered material use); USES (Uses)
(crosslinker; neg.-working electron-beam resist composition containing polysilsesquioxane)

IT 188557-77-9P 475115-04-3P
RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(neg.-working electron-beam resist composition containing polysilsesquioxane)

L19 ANSWER 5 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2005:612362 HCAPLUS Full-text
DN 143:134159
TI Organopolysiloxane curable composition
IN Morita, Yoshitsugu; Isshiki, Minoru; Ueki, Hiroshi; Enami, Hiroji
PA Dow Corning Toray Silicone Co., Ltd., Japan
SO PCT Int. Appl., 31 pp.
CODEN: PIXXD2
DT Patent
LA Japanese
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2005063843	A1	20050714	WO 2004-JP19489	200412 20
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW				
RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
EP 1702938	A1	20060920	EP 2004-807844	200412 20
EP 1702938	B1	20080924		
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, FI, RO, CY, TR, BG, CZ, EE, HU, PL, SK, IS				
CN 1906226	A	20070131	CN 2004-80040671	200412 20

AT 409201	T	20081015	AT 2004-807844	200412 20
KR 2007004594	A	20070109	KR 2006-715037	200607 25
US 20070282058	A1	20071206	US 2007-584655	200707 06
PRAI JP 2003-433628	A	20031226		
WO 2004-JP19489	W	20041220		

AB A silicone composition comprises (A) an organopolysiloxane having a branched-chain structure and containing at least two monovalent hydrocarbon groups with phenolic hydroxyl group, as shown in the general formula [R13SiO1/2]a[R22SiO]b[R3SiO3/2]c (wherein, R1, R2 and R3 are C1-C12 organic groups; a+b+c=1; 0≤a≤0.8; 0≤b≤0.8; 0.2≤c≤1.0); (B) a linear organopolysiloxane containing at least two monovalent hydrocarbon groups with epoxy group but without aromatic ring, as shown in the general formula R73SiO(R82SiO)mSiR73 (wherein, R7 and R8 are C1-C12 organic groups; m is an integer from 1 to 1000); (C) a curing accelerator; and (D) filler. Thus, a silicone composition prepared from 25.0 parts of [Z(CH3)2SiO1/2]0.6[C6H5SiO3/2]0.4 (wherein, Z is 3-(m-hydroxyphenyl)propyl group), 14.0 parts of X-(CH3)2SiO(CH3)2Si-X (wherein, X is 3-glycidoxypropyl), 1.0 part of catalyst HX 3088, and 60.0 parts of silica filler Admafine, shows viscosity of 15 Pa·s, thermal expansion coefficient of 110 ppm/°C, complex viscoelastic modulus of 80 MPa, curing time of 45 min, and good adhesiveness to solder resist, nickel, copper, aluminum and glass.

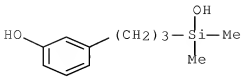
IT 858341-40-9 858341-41-0
RL: POF (Polymer in formulation); PRP (Properties); TEM (Technical or engineered material use); USES (Uses)
(organopolysiloxane curable composition)

RN 858341-40-9 HCAPLUS

CN Silanetriol, phenyl-, polymer with [3-(3-hydroxyphenyl)propyl]dimethylsilanol and 1,1,3,3-tetramethyl-1,3-bis[3-(oxiranylmethoxy)propyl]disiloxane (9CI) (CA INDEX NAME)

CM 1

CRN 858341-39-6
CMF C11 H18 O2 Si

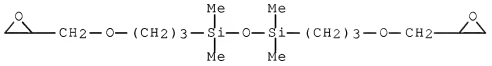


CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

CM 3

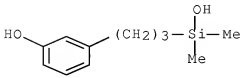
CRN 126-80-7
CMF C16 H34 O5 Si2



RN 858341-41-0 HCAPLUS
CN Silanetriol, phenyl-, polymer with [3-(3-hydroxyphenyl)propyl]dimethylsilanol, 1,1,3,3-tetramethyl-1,3-bis[3-(oxiranylmethoxy)propyl]disiloxane and trimethoxy[3-(oxiranylmethoxy)propyl]silane (9CI) (CA INDEX NAME)

CM 1

CRN 858341-39-6
CMF C11 H18 O2 Si

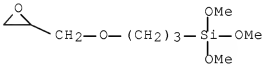


CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

CM 3

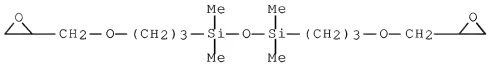
CRN 2530-83-8
CMF C9 H20 O5 Si



CM 4

CRN 126-80-7

CMF C16 H34 O5 Si2



IC ICM C08G059-62
CC 37-6 (Plastics Manufacture and Processing)
IT 858341-40-9 858341-41-0 858341-42-1
RL: POF (Polymer in formulation); PRP (Properties); TEM (Technical or engineered material use); USES (Uses)
(organopolysiloxane curable composition)
RE.CNT 6 THERE ARE 6 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 6 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2004:534428 HCAPLUS Full-text
DN 141:79326
TI Chemical amplification type silicone base positive photoresist composition
IN Hirayama, Taku; Yamada, Tomotaka; Kawana, Daisuke; Tamura, Kouki; Sato, Kazufumi
PA Tokyo Ohka Kogyo Co., Ltd., Japan
SO PCT Int. Appl., 34 pp.
CODEN: PIXXD2
DT Patent
LA Japanese
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2004055598	A1	20040701	WO 2003-JP15344	20031201

W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW
RW: BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AM,

AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG

AU 2003302990	A1	20040709	AU 2003-302990		200312 01
DE 10393820	T5	20051027	DE 2003-10393820		200312 01
TW 282040	B	20070601	TW 2003-92133901		200312 02
US 20060003252	A1	20060105	US 2005-537290		200506 22

PRAI JP 2002-350563 A 20021202
JP 2003-46611 A 20030224
JP 2003-190618 A 20030702
WO 2003-JP15344 W 20031201

AB A chemical amplification type silicone base pos. resist composition that can be produced from easily procurable compds. as raw materials through simple means and can provide a bilayer resist material from which fine pattern of high resolution, high aspect ratio, desirable sectional morphol. and low line edge roughness can be formed. In particular, a chemical amplification type pos. resist composition comprising alkali soluble resin (A) and photoacid generator (B) wherein a ladder type silicone copolymer comprising (hydroxyphenylalkyl)silsesquioxane units (a1), (alkoxyphenylalkyl)silsesquioxane units (a2) and alkyl- or phenylsilsesquioxane units (a3) is used as the alkali soluble resin (A). The copolymer wherein in the component (A), the units (a3) are phenylsilsesquioxane units is a novel compound

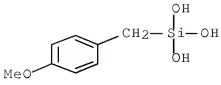
IT 711008-00-3
RL: TEM (Technical or engineered material use); USES (Uses)
(chemical amplification type silicone base pos. photoresist composition)

RN 711008-00-3 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-[(4-methoxyphenyl)methyl]silanetriol and 1-phenylsilanetriol (CA INDEX NAME)

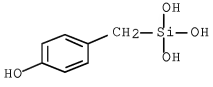
CM 1

CRN 546114-67-4
CMF C8 H12 O4 Si



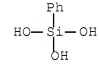
CM 2

CRN 188557-76-8
CMF C7 H10 O4 Si



CM 3

CRN 3047-74-3
CMF C6 H8 O3 Si



IC ICM G03F007-11
ICS C08G077-14; H01L021-027
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 38
ST chem amplification silicone photoresist compn

silsesquioxane
IT Photoresists
(chemical amplification type silicone base pos. photoresist composition)
IT 711008-00-3
RL: TEM (Technical or engineered material use); USES (Uses)
(chemical amplification type silicone base pos. photoresist composition)
IT 102-71-6, Triethanolamine, uses 102-82-9, Tributylamine 1571-33-1, Phenylphosphonic acid
RL: TEM (Technical or engineered material use); USES (Uses)
(quencher; chemical amplification type silicone base pos. photoresist composition)
RE.CNT 18 THERE ARE 18 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 7 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2002:869229 HCAPLUS Full-text
DN 137:377441
TI Photoimageable resist composition containing specific polysilsesquioxane for bilayer resist system
IN Gronbeck, Dana A.; Barclay, George G.; Linehan, Leo L.; Xiong, Kao; Kanagasabapathy, Subareddy
PA Shipley Company, LLC, USA
SO PCT Int. Appl., 65 pp.
CODEN: PIXXD2
DT Patent
LA English
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2002091083	A1	20021114	WO 2002-US14732	200205 08
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZM, ZW				
RW: GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
TW 594416	B	20040621	TW 2002-91109417	200205

07

AU 2002305499 A1 20021118 AU 2002-305499
200205
08

US 20030099899 A1 20030529 US 2002-140761
200205
08

US 6803171 B2 20041012
EP 1407324 A1 20040414 EP 2002-734323
200205
08

R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR

JP 2005507087 T 20050310 JP 2002-588280
200205
08

US 20050026077 A1 20050203 US 2004-924350
200408
23

PRAI US 2001-289368P P 20010508
US 2002-140761 A1 20020508
WO 2002-US14732 W 20020508

AB Disclosed are photoimaging compns. containing silsesquioxane binder polymers and photoactive compds., methods of forming relief images using such compns. and methods of manufacturing electronic devices using such compns. Such compns. are useful as photoresists and in the manufacture of optoelectronic devices.

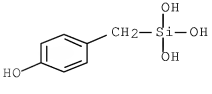
IT 475115-04-9
RL: TEM (Technical or engineered material use); USES (Uses)
(photoimaging composition containing specific polysilsesquioxane)

RN 475115-04-9 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

IC ICM G03F007-029
ICS G03F007-032; G03F007-004; G03C001-725
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
IT Light-sensitive materials
Photoresists
(photoimaging composition containing specific polysilsesquioxane)
IT 475115-04-9
RL: TEM (Technical or engineered material use); USES (Uses)
(photoimaging composition containing specific polysilsesquioxane)
RE.CNT 10 THERE ARE 10 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 8 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 1994:689666 HCAPLUS Full-text
DN 121:289666
OREF 121:52719a,52722a
TI Photoresist composition
IN Kobayashi, Yoshihito
PA Tokyo Shibaura Electric Co, Japan
SO Jpn. Kokai Tokkyo Koho, 41 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 06075377	A	19940318	JP 1992-226130	

PRAI JP 1992-226130 19920825

AB The title composition comprises an alkali-soluble polymer, a compound having a substituent decomposing by an acid, and a photo acid generator, R2SO3CR1R3C.tplbond.CC.tplbond.CCR4R6O3SR5 [R1-6 = aromatic hydrocarbyl, heterocyclyl, aliphatic hydrocarbyl, characteristic group, H]. The composition showed high sensitivity to both deep UV and ionization radiation and was alkali-developable.

IT 159103-14-7 159103-16-9 159103-24-9

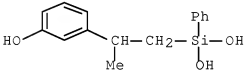
RL: DEV (Device component use); TEM (Technical or engineered material use); USES (Uses)
(deep UV sensitive alkali-developable photoresist composition)

RN 159103-14-7 HCAPLUS

CN Silanediol, diphenyl-, polymer with [2-(3-hydroxyphenyl)propyl]phenylsilanediol (9CI) (CA INDEX NAME)

CM 1

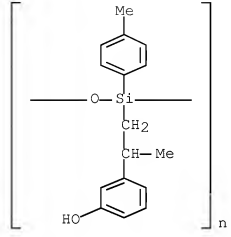
CRN 159103-13-6
CMF C15 H18 O3 Si



CM 2

CRN 947-42-2
CMF C12 H12 O2 Si

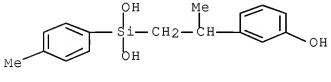
RN 159103-16-9 HCAPLUS
CN Poly[oxy[[2-(3-hydroxyphenyl)propyl](4-methylphenyl)silylene]] (9CI) (CA INDEX NAME)



RN 159103-24-9 HCAPLUS
CN Silanediol, [2-(3-hydroxyphenyl)propyl](4-methylphenyl)-, homopolymer (9CI) (CA INDEX NAME)

CM 1

CRN 159103-23-8
CMF C16 H20 O3 Si



IC ICM G03F007-039
ICS C08K005-42; C08L101-00; G03F007-004; H01L021-312
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 76
ST photoresist compn photo acid generator

IT Polycarbosilanes
Siloxanes and Silicones, uses
RL: DEV (Device component use); TEM (Technical or engineered material use); USES (Uses)
(deep UV sensitive alkali-developable photoresist composition)
IT Phenolic resins, uses
RL: DEV (Device component use); TEM (Technical or engineered material use); USES (Uses)
(novolak, cresol-based, m, p-cresol novolak resin; deep UV sensitive alkali-developable photoresist composition)
IT Resists
(photo-, deep UV sensitive photoresist composition)
IT 24979-70-2, Poly(p-vinylphenol) 159103-11-4 159103-12-5
159103-14-7 159103-15-8 159103-16-9
159103-20-5 159103-22-7 159103-24-9
RL: DEV (Device component use); TEM (Technical or engineered material use); USES (Uses)
(deep UV sensitive alkali-developable photoresist composition)
IT 117458-06-7 127669-88-9 138888-97-8 142952-62-3 143897-55-6
143897-56-7 143897-58-9 143897-61-4 159103-06-7 159103-07-8
159103-17-0 159103-18-1
RL: CAT (Catalyst use); TEM (Technical or engineered material use); USES (Uses)
(development inhibitor in deep UV sensitive alkali-developable photoresist composition)
IT 32527-15-4 73130-96-8 120551-36-2 149873-03-0 149873-13-2
159103-08-9 159103-09-0 159103-10-3
RL: CAT (Catalyst use); TEM (Technical or engineered material use); USES (Uses)
(photo acid generator in deep UV sensitive alkali-developable photoresist composition)

L19 ANSWER 9 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 1989:622152 HCAPLUS Full-text
DN 111:222152
OREF 111:36733a,36736a
TI Photosensitive composition containing azide compound for high-precision pattern
IN Horiguchi, Rumiko; Hayase, Shuzi; Onishi, Yasunobu; Ushirogouchi, Toru
PA Toshiba Corp., Japan
SO Ger. Offen., 36 pp.
CODEN: GWXXBX
DT Patent
LA German

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	DE 3841571	A1	19890629	DE 1988-3841571	19881209
	JP 01154047	A	19890616	JP 1987-312657	19871210
	JP 01154048	A	19890616	JP 1987-312658	19871210
	JP 01161336	A	19890626	JP 1987-320414	19871218
	JP 01241544	A	19890926	JP 1988-68387	19880323
	DE 3844739	C2	19950907	DE 1988-3844739	19881209

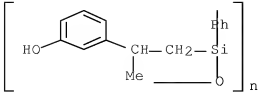
PRAI	JP 1987-312657	A	19871210
	JP 1987-312658	A	19871210
	JP 1987-320414	A	19871218
	JP 1988-68387	A	19880323
	DE 1988-3841571	A3	19881209

AB A photosensitive composition is described containing an alkali-soluble resin, optionally a Si-containing resin, and a compound sensitive to 248 nm deep UV radiation and having the formula R1COC(N2)COR2 [I; R1, R2 = C1-20 alkyl or alkoxy, aryl, aryloxy, anilino]. Optionally the photosensitive compds. are Si-containing compds. of the formula R2R3R4 SiC(N2)R1 [R1-R4 = H, C1-10 alkyl, aryl, silyl]. The preferred compds. of the formula I are aromatic compds. in which ≥1 benzene ring is substituted with ≥1 O2CC(N2)COMe group.

IT 123710-88-3
RL: USES (Uses)
(binder, for deep UV photoresist)

RN 123710-88-3 HCAPLUS

CN Poly[oxy[[2-(3-hydroxyphenyl)propyl]phenylsilylene]] (9CI) (CA INDEX NAME)

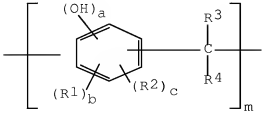


IC ICM G03F007-10
ICS G03F007-08; C08L025-18; C08L061-04
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
ST photosensitive compn photoresist pattern; azide silane photosensitive compd; binder photosensitive compd; phenolic resin photosensitive compd
IT Phenolic resins, uses and miscellaneous
RL: USES (Uses)
(binders, for deep UV photoresist)
IT Binding materials
Azides
RL: USES (Uses)
(for deep UV photoresist)
IT Resists
(photo-, deep UV, azides for)
IT 25086-15-1, Methacrylic acid-methyl methacrylate copolymer 27029-76-1 59269-51-1, Polyvinylphenol 72317-19-2 85229-30-7, Acrylonitrile-isopropenylphenol copolymer 100346-90-5, m-Cresol-p-cresol-formaldehyde-2,5-xylenol copolymer 102868-49-5 104426-15-5 104426-16-6 111634-04-9 112504-03-7, m-Cresol-p-cresol-formaldehyde-3,5-xylenol copolymer 123710-88-3 123737-03-1 123737-04-2 123737-05-3 123737-07-5 123737-09-7
RL: USES (Uses)
(binder, for deep UV photoresist)
IT 2009-96-3 2085-31-6 22760-66-3 24379-49-5 28383-65-5 41657-71-0 75742-13-1 86997-48-0 123131-57-7 123766-64-3 123766-65-4 123766-66-5 123766-67-6 123766-68-7 123766-69-8 123766-70-1 123766-71-2 123766-72-3 123766-73-4 123766-74-5 123766-75-6 123766-76-7 123766-77-8 123766-78-9 123766-79-0 123783-62-0 123783-63-1
RL: USES (Uses)
(photosensitive compound, for deep UV photoresist)
RE.CNT 3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

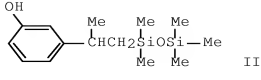
L19 ANSWER 10 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 1989:125491 HCAPLUS Full-text
DN 110:125491
OREF 110:20537a,20540a
TI Photosensitive coating composition containing silicon-containing polymer
IN Horiguchi, Rumiko; Hayase, Shuzi; Onishi, Yasunobu
PA Toshiba Corp., Japan
SO Ger. Offen., 44 pp.
CODEN: GWXXBX
DT Patent
LA German
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	DE 3810247	A1	19881006	DE 1988-3810247	19880325
	DE 3810247	C2	19930128		
	JP 63237052	A	19881003	JP 1987-72113	19870326
	JP 01088447	A	19890403	JP 1987-245497	19870929
	JP 01107254	A	19890425	JP 1987-263965	19871021
	US 5063134	A	19911105	US 1990-455783	19900102
PRAI	JP 1987-72113	A	19870326		
	JP 1987-245497	A	19870929		
	JP 1987-263965	A	19871021		
	US 1988-173546	B1	19880325		

GI



I



II

AB The title composition contains a photosensitive material and a polymer having recurring units of the formula I [R1-R4 = H, alkyl, alkoxy, alkyl; ≥1 of R1-R4 is a Si-containing C1-10 alkyl group; m = pos. integer; a, b = 1-3; c = 0-2; a + b + c ≤ 4]. The material has improved resistance to O plasma and can be used in photolithog. applications. Thus, a mixture of II-m-cresol-p-cresol-HCHO copolymer and 2,3,4-trihydroxybenzophenone bis(1,2-naphthoquinone-2-diazido-5-sulfonate) was used to form a photoresist layer.

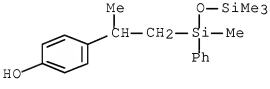
IT 119608-22-9 119608-29-6
RL: USES (Uses)
(photoresist containing)

RN 119608-22-9 HCAPLUS

CN Formaldehyde, polymer with 3-methylphenol and 4-[1-methyl-2-(1,3,3,3-tetramethyl-1-phenyldisiloxanyl)ethyl]phenol (9CI) (CA INDEX NAME)

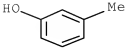
CM 1

CRN 119608-21-8
CMF C19 H28 O2 Si2



CM 2

CRN 108-39-4
CMF C7 H8 O



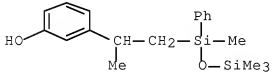
CM 3

CRN 50-00-0
CMF C H2 O

RN 119608-29-6 HCAPLUS
CN Formaldehyde, polymer with 3-methylphenol and 3-[1-methyl-2-(1,3,3,3-tetramethyl-1-phenyldisiloxanyl)ethyl]phenol (9CI) (CA INDEX NAME)

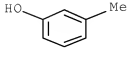
CM 1

CRN 119608-28-5
CMF C19 H28 O2 Si2



CM 2

CRN 108-39-4
CMF C7 H8 O



CM 3

CRN 50-00-0
CMF C H2 O

IC ICM G03F007-00
ICS G03F007-08; G03C001-72
ICA C08L061-04; C09D003-54; C09D003-81; H01L021-312
CC 74-6 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
ST photolithog silicon contg polymer photoresist
IT Resists
(photo-, silicon-containing polymer for)
IT Phenolic resins, uses and miscellaneous
RL: USES (Uses)
(silicon-containing, photoresists containing)
IT 119588-16-8 119588-17-9 119588-19-1 119588-20-4 119588-21-5
119588-23-7 119588-25-9 119588-27-1 119588-29-3 119588-30-6
119588-31-7 119588-32-8 119588-34-0 119588-35-1 119608-20-7
119608-22-9 119608-23-0 119608-25-2 119608-27-4
119608-29-6 119608-31-0 119608-32-1 119608-33-2
119608-34-3 119608-35-4 119608-37-6 119608-38-7 119608-40-1
RL: USES (Uses)
(photoresist containing)
IT 75578-77-7 75578-79-9 75742-13-1 109478-62-8 119564-70-4
RL: USES (Uses)
(photoresist containing Si-containing polymer and)
RE.CNT 1 THERE ARE 1 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

=> d l22 1-5 bib abs hitstr hitind

L22 ANSWER 1 OF 5 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2008:447443 HCAPLUS Full-text
DN 148:427784
TI Curable silicone composition and cured body thereof
IN Morita, Yoshitsugu; Kato, Tomoko; Ueki, Hiroshi
PA Dow Corning Toray Co., Ltd., Japan
SO PCT Int. Appl., 30pp.
CODEN: PIXXD2
DT Patent
LA English
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2008041459	A1	20080410	WO 2007-JP67770	20070905
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
JP 2008081676	A	20080410	JP 2006-265955	20060928

PRAI JP 2006-265955 A 20060928

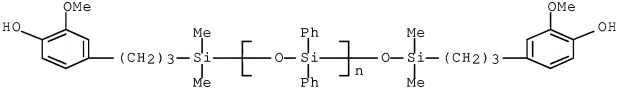
AB A curable silicone composition comprises: (A) a diorganopolysiloxane represented by the following general formula: XR2(R12SiO)mR12SiR2X [where R1 designates a monovalent hydrocarbon group that has six or fewer carbon atoms and is free of aliphatic unsatd. bonds; R2 designates an alkylene group; and X is an organopolysiloxane residue represented by the following average unit formula: (YR12SiO1/2)a(SiO4/2)b (where R1 is the same as defined above; Y is a single bond, a hydrogen atom, a group represented by aforementioned R1, an epoxy-containing alkyl group, an alkoxysilylalkyl group, or an alkyl group with seven or more carbon atoms; however, in one mol., at least one Y is a single bond, and at least one Y is an alkyl group with seven or more carbon atoms; "a" is a pos. number; "b" is a pos. number; and "a/b" is a number in the range of 0.2 to 4.0), the aforementioned group represented by R1 or an alkenyl group; however,

at least one X is the aforementioned organopolysiloxane residue; and "m" is an integer equal to or greater than 1] and (B) a curing agent for epoxy resin. The composition has good handleability and, when cured, forms a cured silicone body having low modulus of elasticity.

IT 537708-34-2
RL: TEM (Technical or engineered material use); USES (Uses)
(curable silicone composition and cured body thereof)

RN 537708-34-2 HCAPLUS

CN Poly[oxy(diphenylsilylene)], α-[[3-(4-hydroxy-3-methoxyphenyl)propyl]dimethylsilyl]-ω-[[[3-(4-hydroxy-3-methoxyphenyl)propyl]dimethylsilyl]oxy]- (CA INDEX NAME)



CC 37-6 (Plastics Manufacture and Processing)

IT Crosslinking agents
(curable silicone composition and cured body thereof)

IT 106-92-3, Allylglycidylether 112-88-9, 1-Octadecene 872-05-9, 1-Decene 2551-83-9, Allyltrimethoxysilane 25068-38-6, Bisphenol-A epoxy resin 58421-55-9 158167-48-7
537708-34-2
RL: TEM (Technical or engineered material use); USES (Uses)
(curable silicone composition and cured body thereof)

RE.CNT 3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 2 OF 5 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2008:353339 HCAPLUS Full-text

DN 148:356589

TI Thermally conductive, curable silicone composition and electronic component

IN Morita, Yoshitsugu; Isshiki, Minoru; Kato, Tomoko

PA Dow Corning Toray Co., Ltd., Japan

SO PCT Int. Appl., 34pp.
CODEN: PIXXD2

DT Patent

LA English

FAN.CNT 1

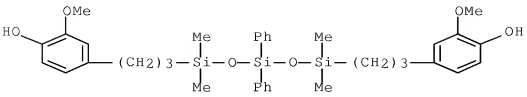
	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	WO 2008032575	A1	20080320	WO 2007-JP66829	20070823
	W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
	RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
	JP 2008063542	A	20080321	JP 2006-246080	20060911
PRAI	JP 2006-246080	A	20060911		

AB A curable silicone composition comprising at least the following components: (A) an epoxy-containing organopolysiloxane; (B) a curing agent for an epoxy resin; (C) a thermally conductive metal powder; and (D) a thermally conductive nonmetal powder; exhibits low viscosity, excellent handleability and curability and, when cured, forms a cured body of flexibility, low sp. gr., and excellent thermal conductivity An electronic component sealed or adhesively bonded with use of a cured body obtained by curing the aforementioned composition provides high reliability.

IT 910040-29-8
RL: TEM (Technical or engineered material use); USES (Uses) (thermally conductive, curable silicone composition and electronic component)

RN 910040-29-8 HCAPLUS

CN Phenol, 4,4'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bis[2-methoxy- (CA INDEX NAME)



CC 37-6 (Plastics Manufacture and Processing)
Section cross-reference(s): 76
IT Adhesives
Crosslinking agents
Sealing compositions
Semiconductor devices
(thermally conductive, curable silicone composition and electronic component)
IT 9016-00-6D, Polydimethylsiloxane, hydroxyphenyl-terminated
910040-29-8
RL: TEM (Technical or engineered material use); USES (Uses)
(thermally conductive, curable silicone composition and electronic component)
RE.CNT 5 THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 3 OF 5 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2007:993056 HCAPLUS Full-text
DN 147:345203
TI Semiconductor devices with good scratch resistance and low warpage and their manufacture
IN Morita, Koji; Isshiki, Minoru; Ueki, Hiroshi; Kato, Tomoko
PA Dow Corning Toray Co., Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 28pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2007224146	A	20070906	JP 2006-46872	20060223
	WO 2007099823	A1	20070907	WO 2007-JP53131	20070214

W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW

RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM

EP 1986832 A1 20081105 EP 2007-714631 200702 14

R: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LI, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR

KR 2008108089 A 20081211 KR 2008-720670 200808 22

PRAI JP 2006-46872 A 20060223

WO 2007-JP53131 W 20070214

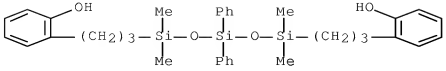
AB The manufacturing method includes setting semiconductor devices in molds, feeding curable silicone compns. between the molds and the devices, and compression-molding so as to package, wherein the compns. include epoxy-containing silicones and curing agents. Thus, a composition with viscosity at 25° 140 Pa-s and complex modulus 730 MPa comprising XCH2CH2(Me2SiO)33Me2SiCH2CH2X [X is siloxane residue of (GMe2SiO1/2)9(-Me2SiO1/2)1(SiO4/2)6, G is 3-glycidoxypropyl] 31.0, 2,2'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bisphenol 14.0, capsulated amine curing accelerator (HX 3721) 10.0, spherical amorphous silica (Admafine) 60.0, and 3-glycidoxypropyltrimethoxysilane 1 part was applied on a semiconductor chip-mounted circuit board, compression-molded, and heated to give a packaged device showing thickness difference between the central and circumferential parts <5% and warpage 2 mm.

IT 910040-28-7 910040-29-8

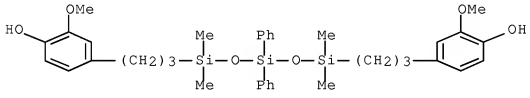
RL: RCT (Reactant); RACT (Reactant or reagent)
(crosslinker; manufacture of semiconductor devices with good scratch resistance and low warpage)

RN 910040-28-7 HCAPLUS

CN Phenol, 2,2'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bis- (CA INDEX NAME)



RN 910040-29-8 HCAPLUS
CN Phenol, 4,4'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bis[2-methoxy- (CA INDEX NAME)



CC 38-3 (Plastics Fabrication and Uses)
Section cross-reference(s): 76
IT Polysiloxanes, uses
RL: POF (Polymer in formulation); TEM (Technical or engineered material use); USES (Uses)
(di-Me, epoxy-containing, crosslinked; manufacture of semiconductor devices with good scratch resistance and low warpage)
IT Silsesquioxanes
RL: POF (Polymer in formulation); TEM (Technical or engineered material use); USES (Uses)
(epoxy-containing, crosslinked; manufacture of semiconductor devices with good scratch resistance and low warpage)
IT Coupling agents
Crosslinking catalysts
Electronic packaging materials
Fillers
Semiconductor device fabrication
(manufacture of semiconductor devices with good scratch resistance and low warpage)
IT 25068-38-6, Epikote 828 51350-55-1D, Phenylsilanetriol homopolymer, ladder sru, dimethyl(3-glycidoxy)propylsilyl-terminated 157374-41-9D, Phenylsilanetriol homopolymer,

dimethyl(glycidoxy)propylsilyl-terminated
RL: POF (Polymer in formulation); TEM (Technical or engineered material use); USES (Uses)
(crosslinked; manufacture of semiconductor devices with good scratch resistance and low warpage)

IT 9016-00-6D, Poly[oxy(dimethylsilylene)], dimethyl[3-(o-hydroxyphenyl)propyl]silyl-terminated 31900-57-9D, Dimethylsilanediol homopolymer, dimethyl[3-(o-hydroxyphenyl)propyl]silyl-terminated 910040-28-7 910040-29-8
RL: RCT (Reactant); RACT (Reactant or reagent)
(crosslinker; manufacture of semiconductor devices with good scratch resistance and low warpage)

L22 ANSWER 4 OF 5 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2006:978171 HCAPLUS Full-text
DN 145:357617
TI Curable silicone composition and electronic device produced therefrom
IN Morita, Yoshitsugu; Isshiki, Minoru; Ueki, Hiroshi; Kato, Tomoko
PA Dow Corning Toray Co., Ltd., Japan
SO PCT Int. Appl., 38pp.
CODEN: PIXXD2
DT Patent
LA English
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2006098493	A1	20060921	WO 2006-JP305639	200603 15
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW				
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
JP 2006257115	A	20060928	JP 2005-72395	200503 15

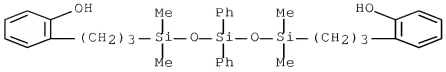
EP 1858983 A1 20071128 EP 2006-729606
200603
15
EP 1858983 B1 20080917
R: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LI, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR
AT 408649 T 20081015 AT 2006-729606
200603
15
KR 2007117597 A 20071212 KR 2007-721226
200709
14
CN 101142280 A 20080312 CN 2006-80008265
200709
14
PRAI JP 2005-72395 A 20050315
WO 2006-JP305639 W 20060315

AB A curable silicone composition comprising: (A) a diorganosiloxane represented by the following general formula: AR2(R12SiO)nR12SiR2A {wherein R1 represents the same or different optionally substituted univalent hydrocarbon groups that do not have unsatd. aliphatic bonds; R2 represents bivalent organic groups; A designates siloxane residual radicals represented by the following average unit formula: (XR12SiO1/2)a(SiO4/2)b (wherein R1 designates the previously mentioned group; X designates a single bond, hydrogen atom, the previously mentioned group that is designated by R1, an epoxy-containing alkyl group, or an alkoxysilylalkyl group; at least one X in one mol. is a single bond; at least two X's are epoxy-containing alkyl groups; a is a pos. number, b is a pos. number; and a/b is a pos. number within the range of 0.2 to 4), and n is an integer which is equal to or greater than 1}; and (B) a curing agent for an epoxy resin, is characterized by excellent handle ability and curability and that is suitable for curing into a cured body that has excellent flexibility and adhesive characteristics; to provide a highly reliable electronic device. Typical (B) is a phenolic compound, and, the composition contains an amine-type accelerator.

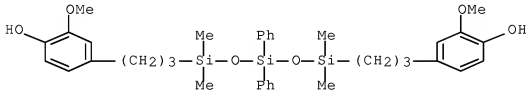
IT 910040-28-7 910040-29-8
RL: MOA (Modifier or additive use); TEM (Technical or engineered material use); USES (Uses)
(crosslinking agent; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture of electronic devices)

RN 910040-28-7 HCAPLUS

CN Phenol, 2,2'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bis- (CA INDEX NAME)



RN 910040-29-8 HCAPLUS
CN Phenol, 4,4'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bis[2-methoxy- (CA INDEX NAME)



CC 37-6 (Plastics Manufacture and Processing)
Section cross-reference(s): 76
IT Phenols, uses
RL: MOA (Modifier or additive use); TEM (Technical or engineered material use); USES (Uses)
(crosslinking agent; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture of electronic devices)
IT Amines, uses
RL: CAT (Catalyst use); USES (Uses)
(crosslinking catalyst; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture of electronic devices)
IT 2530-83-8, 3-Glycidyloxypropyltrimethoxysilane 25068-38-6, Epikote 828
RL: MOA (Modifier or additive use); TEM (Technical or engineered material use); USES (Uses)
(addnl. crosslinkable component; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture

of electronic devices)
IT 910107-81-2, Silicic acid, dimethyl-3-(glycidyloxy)propylsilyl ester
RL: TEM (Technical or engineered material use); USES (Uses)
(addnl. crosslinkable component; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture
of electronic devices)
IT 25550-51-0, HN-5500 27924-97-6, MEH 8000 31900-57-9D, Dimethylsilanediol homopolymer, hydroxyphenyl-terminated
158167-48-7 163617-00-3 191875-74-8 910040-28-7
910040-29-8
RL: MOA (Modifier or additive use); TEM (Technical or engineered material use); USES (Uses)
(crosslinking agent; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture of electronic
devices)
IT 288-32-4D, Imidazole, derivs. 134633-76-4, HX 3721 146702-27-4, HX 3941HP 149779-74-8, HX 3088 910113-00-7, HXA 4921HP
910113-01-8, Amicure PN 3
RL: CAT (Catalyst use); USES (Uses)
(crosslinking catalyst; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture
of electronic devices)
RE.CNT 5 THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 5 OF 5 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 1997:276826 HCAPLUS Full-text
DN 126:344382
OREF 126:66967a,66970a
TI Hybrid Organic/Inorganic Copolymers with Strongly Hydrogen-Bond Acidic Properties for Acoustic Wave and Optical Sensors
AU Grate, Jay W.; Kaganove, Steven N.; Patrash, Samuel J.; Craig, Richard; Bliss, Mary
CS Environmental Molecular Sciences Laboratory Engineering and Analytic Sciences Department, Pacific Northwest National Laboratory, Richland, WA, 99352, USA
SO Chemistry of Materials (1997), 9(5), 1201-1207
CODEN: CMATEX; ISSN: 0897-4756
PB American Chemical Society
DT Journal
LA English
AB Hybrid organic/inorg. polymers have been prepared incorporating fluoroalkyl-substituted bisphenol groups linked using oligosiloxane spacers. These hydrogen-bond acidic materials have glass-to-rubber

transition temps. below room temperature and are excellent sorbents for basic vapors. The phys. properties such as viscosity and refractive index can be tuned by varying the length of the oligosiloxane spacers and the mol. weight In addition, the materials are easily cross-linked to yield solid elastomers. The potential use of these materials for chemical sensing has been demonstrated by applying them to surface acoustic wave devices as thin films and detecting the hydrogen-bond basic vapor di-Me methylphosphonate with high sensitivity. It has also been demonstrated that one of these materials with suitable viscosity and refractive index can be used to clad silica optical fibers; the cladding was applied to freshly drawn fiber using a fiber drawing tower. These fibers have potential as evanescent wave optical fiber sensors.

IT 189892-82-8P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)
(rubber; preparation of hybrid organic/inorg. siloxane elastomers with strongly hydrogen-bond acidic properties for acoustic wave and optical sensors)

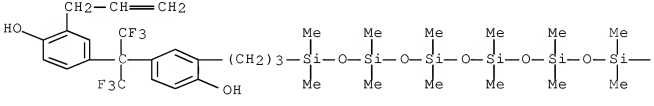
RN 189892-82-8 HCAPLUS

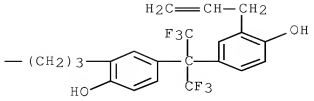
CN Phenol, 4,4'-[(1,1,3,3,5,5,7,7,9,9,11,11-dodecamethyl-1,11-hexasiloxanediyl)bis[3,1-propanediyl(4-hydroxy-3,1-phenylene)[2,2,2-trifluoro-1-(trifluoromethyl)ethylidene]]]bis[2-(2-propenyl)-, polymer with 3-[(dimethylsilyl)oxy]-1,1,5,5-tetramethyl-3-phenyltrisiloxane (9CI) (CA INDEX NAME)

CM 1

CRN 189892-81-7
CMF C54 H74 F12 O9 Si6

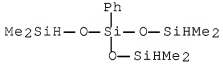
PAGE 1-A





CM 2

CRN 18027-45-7
CMF C12 H26 O3 Si4



CC 39-15 (Synthetic Elastomers and Natural Rubber)
Section cross-reference(s): 38, 73

ST elastomeric fluoro siloxane crosslinkable polymer prepn; cladding bisallyl hexafluorobisphenol terminated crosslinked siloxane; surface acoustic wave sensor hybrid siloxane; sorbent crosslinked bisallylhexafluoro bisphenol siloxane copolymer

IT Crosslinking
Glass transition temperature
Surface acoustic wave sensors
(preparation of hybrid organic/inorg. siloxane elastomers with strongly hydrogen-bond acidic properties for acoustic wave and optical sensors)

IT 170346-91-5, PC 085
RL: CAT (Catalyst use); USES (Uses)
(crosslinking catalyst; preparation of hybrid organic/inorg. siloxane elastomers with strongly hydrogen-bond acidic properties for acoustic wave and optical sensors)

IT 139832-82-8P
RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(rubber; preparation of hybrid organic/inorg. siloxane elastomers with
strongly hydrogen-bond acidic properties for acoustic wave and optical sensors)
RE.CNT 38 THERE ARE 38 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

=> d l27 1-6 bib abs hitstr hitind
YOU HAVE REQUESTED DATA FROM FILE 'HCAPLUS' - CONTINUE? (Y)/N:y

L27 ANSWER 1 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2008:1280393 HCAPLUS Full-text
DN 149:472683
TI Film forming composition for nanoimprinting, process for production of structures, and structures
IN Takeuchi, Yoshiyuki; Ishikawa, Kiyoshi
PA Tokyo Ohka Kogyo Co., Ltd., Japan
SO PCT Int. Appl., 37pp.
CODEN: PIXXD2
DT Patent
LA Japanese
FAN.CNT 2

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2008126523	A1	20081023	WO 2008-JP53988	200803 05

W: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM

JP 2008246876	A	20081016	JP 2007-91695	200703

PRAI JP 2007-91695 A 20070330
JP 2007-227089 A 20070831
JP 2007-227090 A 20070831

AB The film-forming composition for nanoimprinting which permits high-precision pattern transfer from a mold and is good in the close adhesion to a substrate and the peelability of a mold, comprises silsesquioxane resin having structure unit -[Si(R2-p-C6H4OR1)O3/2]- (R1 = H, C1-5 alkyl; R2 = mono-bond, C1-5 alkylene). A process for the production of structures with improved thermal stability comprises coating a base with the film-forming composition to form a film; molding; and peeling the resin layer from the mold. Further, after the peeling of a mold in the production of a structure, it is preferable to irradiate the resin layer with UV light under a reduced pressure.

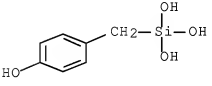
IT 475115-04-9P 1002099-61-7P
RL: IMF (Industrial manufacture); PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PREP (Preparation); PROC (Process); USES (Uses)
(silsesquioxane resin film forming composition for nanoimprinting)

RN 475115-04-9 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8
CMF C7 H10 O4 Si



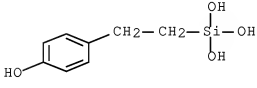
CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

RN 1002099-61-7 HCAPLUS
CN Silanetriol, 1-[2-(4-hydroxyphenyl)ethyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 546114-69-6
CMF C8 H12 O4 Si



CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

CC 38-3 (Plastics Fabrication and Uses)
Section cross-reference(s): 74
IT 51350-55-1P, Phenylsilanetriol homopolymer, ladder sru 157374-41-9P, Phenylsilanetriol homopolymer 475115-04-9P 1002099-61-7P 1043891-50-4P 1043891-51-5P

1071872-66-6P 1071872-67-7P 1071872-68-8P 1071872-69-9P
1071872-70-2P
RL: IMF (Industrial manufacture); PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PREP (Preparation); PROC (Process); USES (Uses)
(silsesquioxane resin film forming composition for nanoimprinting)
RE.CNT 5 THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L27 ANSWER 2 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2008:941189 HCAPLUS Full-text
DN 149:235625
TI Photosensitive composition and method for forming planarization insulating film for liquid crystal display element
IN Takeuchi, Yoshiyuki
PA Tokyo Ohka Kogyo Co., Ltd., Japan
SO PCT Int. Appl., 52pp.
CODEN: PIXXD2
DT Patent
LA Japanese
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2008093629	A1	20080807	WO 2008-JP51179	20080128
W: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
JP 2008191270	A	20080821	JP 2007-23510	200702 01
PRAI JP 2007-23510	A	20070201		

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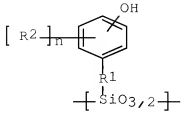


I

AB The composition for forming a planarization insulating film for liquid crystal display (LCD) element contains a resin containing a constituent unit I (R1 = single bond, straight or branched chain alkylene group; R2 = alkyl; n = 0-4) and a constituent unit RSiO3/2 (R = aryl or alkyl), and a sensitizer. The composition enables to form a planarization insulating film having excellent transparency and heat resistance.

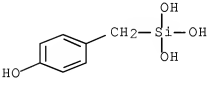
IT 475115-04-9 1002099-61-7
RL: TEM (Technical or engineered material use); USES (Uses)
(assumed monomers; method and compns. for forming heat-resistant transparent planarization insulating films for liquid crystal display elements)

RN 475115-04-9 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8
CMF C7 H10 O4 Si



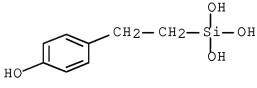
CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

RN 1002099-61-7 HCAPLUS
CN Silanetriol, 1-[2-(4-hydroxyphenyl)ethyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 546114-69-6
CMF C8 H12 O4 Si



CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

CC 74-13 (Radiation Chemistry, Photochemistry, and Photographic and

Other Reprographic Processes)
Section cross-reference(s): 76
IT 475115-04-9 1002099-61-7 1043891-50-4
RL: TEM (Technical or engineered material use); USES (Uses)
(assumed monomers; method and compns. for forming heat-resistant transparent planarization insulating films for liquid crystal display elements)
RE.CNT 7 THERE ARE 7 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L27 ANSWER 3 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2008:90854 HCAPLUS Full-text
DN 148:179495
TI High-refractive-index materials
IN Takeuchi, Yoshiyuki
PA Tokyo Ohka Kogyo Co., Ltd., Japan
SO PCT Int. Appl., 21pp.
CODEN: PIXXD2
DT Patent
LA Japanese
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2008010415	A1	20080124	WO 2007-JP63364	20070704
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
JP 2008024832	A	20080207	JP 2006-199237	200607 21

PRAI JP 2006-199237 A 20060721
AB The high-refractive-index materials contain a siloxane resin having a structural unit R1R2mSiO(3-m)/2 (R1 = hydrocarbon group; R2 = H, hydrocarbon group; m = 0, 1). The materials enable to form a

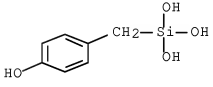
waveguide by a simpler method. Also disclosed are a high-refractive-index member made from the materials, and an image sensor.

IT 475115-04-9 1002099-61-7
RL: TEM (Technical or engineered material use); USES (Uses)
(high-refractive-index materials for optical waveguides and image sensors)

RN 475115-04-9 HCAPLUS
CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8
CMF C7 H10 O4 Si



CM 2

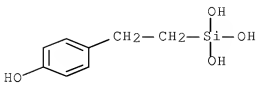
CRN 3047-74-3
CMF C6 H8 O3 Si

RN 1002099-61-7 HCAPLUS
CN Silanetriol, 1-[2-(4-hydroxyphenyl)ethyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 546114-69-6

CMF C8 H12 O4 Si



CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

CC 74-13 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 73
IT 9016-00-6, Polydimethylsilanediol, sru 31900-57-9, Polydimethylsilanediol 51350-55-1, Phenyl silsesquioxane 157374-41-9, Phenyl silsesquioxane 475115-04-9 1002099-61-7 1002099-65-1
RL: TEM (Technical or engineered material use); USES (Uses)
(high-refractive-index materials for optical waveguides and image sensors)
RE.CNT 8 THERE ARE 8 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L27 ANSWER 4 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2007:964078 HCAPLUS Full-text
DN 147:312575
TI Method for manufacturing organic semiconductor device and composition for forming insulating film used therein
IN Ogata, Toshiyuki; Kawana, Daisuke; Hada, Hideo; Takahashi, Motoki; Ohmori, Yutaka; Kajii, Hirotake

PA Tokyo Ohka Kogyo Co., Ltd., Japan; Osaka University
SO PCT Int. Appl., 43pp.
CODEN: PIXXD2
DT Patent
LA Japanese
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI WO 2007097212	A1	20070830	WO 2007-JP52345	20070209
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
JP 2007258663	A	20071004	JP 2006-221829	200608 16

PRAI JP 2006-45273 A 20060222
JP 2006-221829 A 20060816

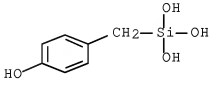
AB Disclosed is a composition for forming an insulating film, which is capable of reducing spaces between mols., thereby forming a dense insulating film. Also disclosed are an insulating film and an organic semiconductor device which can be driven at a low voltage while having a stable driving voltage by using such an insulating film. Specifically disclosed is a composition for forming an insulating film between a gate electrode layer and an organic semiconductor film layer in an organic semiconductor device, which composition contains a resin component (A) having a silsesquioxane backbone. The resin component (A) is composed of a resin (A1) having a structural unit represented by the general formula -(-SiO3/2((R2)n-X-OR1)-)-, where, X represents an alkylene group having 1-15 C atoms or a divalent aromatic hydrocarbon group having 6-15 C atoms; R1 represents a H atom, an alkyl group having 1-15 C atoms or an alkoxyalkyl group having 2-15 C atoms; R2 represents an alkyl group having 1-4 C atoms; and n represents 0 or 1.

IT 475115-04-9
RL: TEM (Technical or engineered material use); USES (Uses)

(method for manufacturing organic TFT and composition for forming insulating
film used therein)
RN 475115-04-9 HCAPLUS
CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si

CC 76-3 (Electric Phenomena)
IT 2386-87-0 3089-11-0 17464-88-9 151271-43-1,
α,ω-Dihexyl-sexithiophene 160848-22-6 193345-23-2
475115-04-9 711008-00-3 882004-77-5 947265-31-8
RL: TEM (Technical or engineered material use); USES (Uses)
(method for manufacturing organic TFT and composition for forming insulating
film used therein)
RE.CNT 30 THERE ARE 30 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L27 ANSWER 5 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2005:672696 HCAPLUS Full-text
DN 143:176216
TI Solid electrolyte proton conductor membrane electrode assembly for fuel cell
IN Wariishi, Koji; Ono, Michio; Nomura, Kimiatsu
PA Fuji Photo Film Co., Ltd., Japan
SO U.S. Pat. Appl. Publ., 36 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 2

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 20050164063	A1	20050728	US 2004-969530	20041020
	JP 2005248152	A	20050915	JP 2004-289019	20040930
PRAI	JP 2003-359927	A	20031020		
	JP 2004-25055	A	20040202		

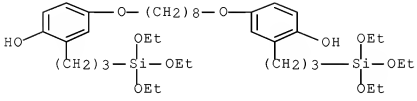
AB A solid electrolyte having a high ionic conductivity and not so much troubled by methanol-crossover through it is provided according to a method of sulfonation of a compound of the formula [((R1O)mSi(R2)3-mL1)nAr1]pL2 wherein R1 represents H, an alkyl group, an aryl group or a silyl group; R2 represents an alkyl group, an aryl group or a heterocyclic group; m indicates an integer of from 1 to 3; L1 represents a single bond, an alkylene group, -O-, -CO-, or a divalent linking group of a combination of any of these groups; L2 represents an n-valent linking group; Ar1 represents an arylene or heteroarylene group having at least one electron-donating group; p indicates an integer of from 2 to 4; n indicates an integer of 1 or 2 followed by sol-gel reaction of the resulting compound, or according to a method of the sol-gel reaction followed by the sulfonation.

IT 861098-58-0DP, sulfonated
RL: DEV (Device component use); SPN (Synthetic preparation); PREP (Preparation); USES (Uses)
(solid electrolyte proton conductor membrane electrode assembly for fuel cell)

RN 861098-58-0 HCAPLUS
CN Phenol, 4,4'-[1,8-octanediylbis(oxy)]bis[2-[3-(triethoxysilyl)propyl]-, polymer with triethoxyphenylsilane (9CI) (CA INDEX NAME)

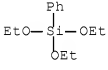
CM 1

CRN 861098-54-6
CMF C38 H66 O10 Si2



CM 2

CRN 780-69-8
CMF C12 H20 O3 Si



IC ICM H01M008-10
ICS C07F007-04
INCL 429033000; 556482000
CC 52-2 (Electrochemical, Radiational, and Thermal Energy Technology)
Section cross-reference(s): 47
IT 51350-55-1DP, sulfonated 124741-08-8DP, sulfonated
141087-51-6DP, sulfonated 152791-93-0DP, sulfonated
852921-77-8DP, sulfonated 852921-78-9DP, sulfonated
861098-36-4DP, sulfonated 861098-37-5DP, sulfonated
861098-38-6DP, sulfonated 861098-39-7DP, sulfonated
861098-40-0DP, sulfonated 861098-41-1DP, sulfonated
861098-43-3DP, sulfonated 861098-44-4DP, sulfonated
861098-46-6DP, sulfonated 861098-47-7DP, sulfonated
861098-48-8DP, sulfonated 861098-49-9DP, sulfonated
861098-50-2DP, sulfonated 861098-53-5DP, sulfonated
861098-55-7DP, sulfonated 861098-57-9DP, sulfonated

861098-58-9DP, sulfonated 861098-60-4DP, sulfonated
861098-62-6DP, sulfonated 861098-63-7DP, sulfonated
861098-64-8DP, sulfonated 861098-65-9DP, sulfonated
861098-66-0DP, sulfonated 861098-67-1DP, sulfonated
RL: DEV (Device component use); SPN (Synthetic preparation); PREP (Preparation); USES (Uses)
(solid electrolyte proton conductor membrane electrode assembly for fuel cell)

L27 ANSWER 6 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 1996:745487 HCAPLUS Full-text
DN 126:13061
OREF 126:2645a,2648a
TI Electrophotographic photoreceptor with uppermost layer containing polyester with siloxane structure
IN Itami, Akihiko; Asano, Masanari
PA Konishiroku Photo Ind, Japan
SO Jpn. Kokai Tokkyo Koho, 43 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

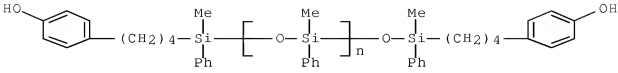
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 08234468	A	19960913	JP 1995-37062	19950224
PRAI JP 1995-37062		19950224		

AB The uppermost layer contains a copolymer with polyester-polycarbonate and polysiloxane structures or polyester with polysiloxane structure. The photoreceptor shows with sensitivity, abrasion resistance, and printing durability.
IT 184155-93-9
RL: DEV (Device component use); USES (Uses)
(electrophotog. photoreceptor with uppermost layer containing polyester with siloxane structure)
RN 184155-93-9 HCAPLUS
CN Benzoic acid, 4,4'-methylenebis-, polymer with α-[[4-(4-hydroxyphenyl)butyl]methylphenylsilyl]-ω-[[[4-(4-hydroxyphenyl)butyl]methylphenylsilyl]oxy]poly[oxy(methylphenylsilylene)] (9CI) (CA INDEX NAME)

CM 1

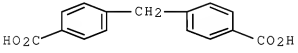
CRN 184155-92-8
CMF (C7 H8 O Si)n C34 H42 O3 Si2

CCI PMS



CM 2

CRN 790-83-0
CMF C15 H12 O4



IC ICM G03G005-147
ICS G03G005-05
CC 74-3 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 38
IT 184155-65-5 184155-66-6 184155-67-7 184155-68-8 184155-70-2
184155-71-3 184155-75-7 184155-77-9 184155-79-1 184155-80-4
184155-82-6 184155-84-8 184155-86-0 184155-88-2 184155-90-6
184155-91-7 184155-93-9 184155-95-1 184155-96-2
184155-97-3 184155-98-4 184156-00-1 184156-03-4 184156-04-5
184156-05-6 184156-06-7 184156-07-8 184156-09-0 184156-12-5
184156-15-8 184156-17-0 184156-19-2 184156-21-6 184156-23-8
184156-46-5
RL: DEV (Device component use); USES (Uses)
(electrophotog. photoreceptor with uppermost layer containing polyester with siloxane structure)

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